

# 2SC4546

Silicon NPN Triple Diffused Planar Transistor (High Voltage and Ultra-high Speed Switching Transistor) Application : Switching Regulator, Lighting Inverter and General Purpose

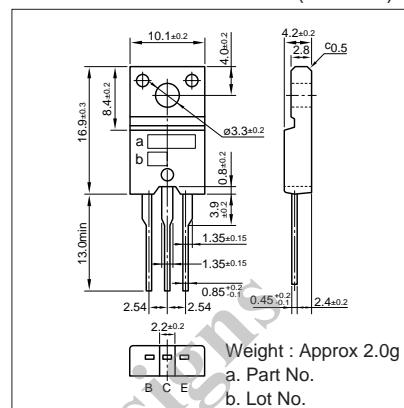
## Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V <sub>CBO</sub>	600	V
V <sub>CEO</sub>	400	V
V <sub>EBO</sub>	7	V
I <sub>c</sub>	7(Pulse14)	A
I <sub>b</sub>	2	A
P <sub>c</sub>	30(Tc=25°C)	W
T <sub>j</sub>	150	°C
T <sub>tsg</sub>	-55 to +150	°C

## Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I <sub>CO</sub>	V <sub>CB</sub> =600V	100max	μA
I <sub>EO</sub>	V <sub>EB</sub> =7V	100max	μA
V <sub>(BR)CEO</sub>	I <sub>c</sub> =25mA	400min	V
h <sub>FE</sub>	V <sub>CE</sub> =4V, I <sub>c</sub> =3A	10to25	
V <sub>CE(sat)</sub>	I <sub>c</sub> =3A, I <sub>b</sub> =0.6A	0.7max	V
V <sub>BE(sat)</sub>	I <sub>c</sub> =3A, I <sub>b</sub> =0.6A	1.3max	V
f <sub>r</sub>	V <sub>CE</sub> =12V, I <sub>e</sub> =-0.5A	10typ	MHz
C <sub>OB</sub>	V <sub>CB</sub> =10V, f=1MHz	55typ	pF

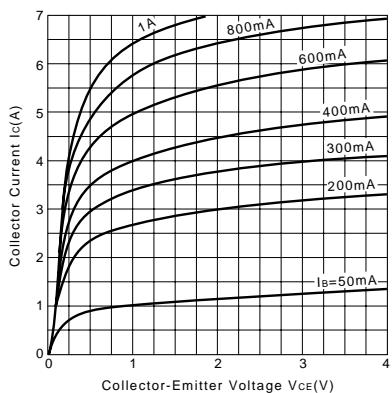
## External Dimensions FM20(TO220F)



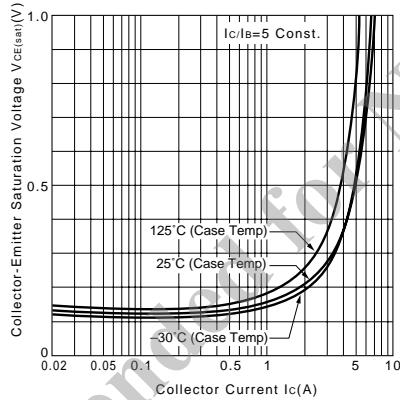
## Typical Switching Characteristics (Common Emitter)

V <sub>CC</sub> (V)	R <sub>L</sub> (Ω)	I <sub>c</sub> (A)	V <sub>BB1</sub> (V)	V <sub>BB2</sub> (V)	I <sub>B1</sub> (A)	I <sub>B2</sub> (A)	t <sub>on</sub> (μs)	t <sub>tsg</sub> (μs)	t <sub>f</sub> (μs)
200	67	3	10	-5	0.6	-1.2	0.5max	2max	0.15max

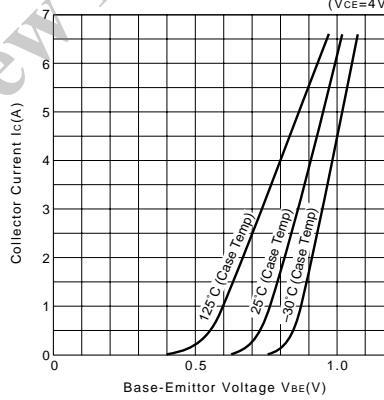
## I<sub>c</sub>-V<sub>CE</sub> Characteristics (Typical)



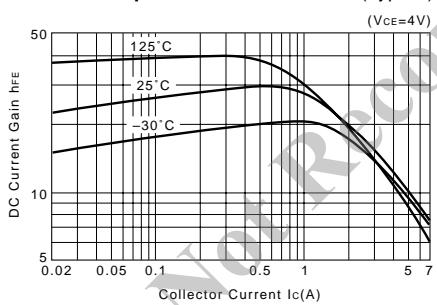
## V<sub>CE(sat)</sub>-I<sub>c</sub> Characteristics (Typical)



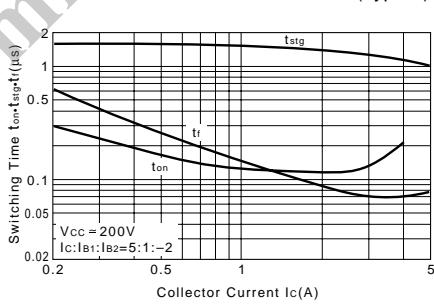
## I<sub>c</sub>-V<sub>BE</sub> Temperature Characteristics (Typical)



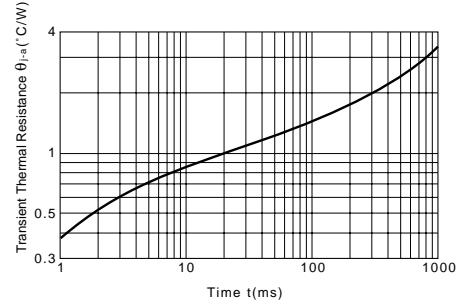
## h<sub>FE</sub>-I<sub>c</sub> Temperature Characteristics (Typical)



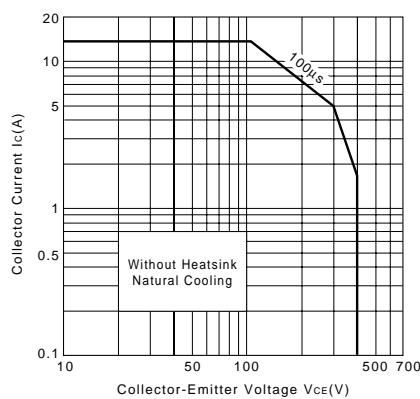
## t<sub>on</sub>•t<sub>tsg</sub>•t<sub>f</sub>-I<sub>c</sub> Characteristics (Typical)



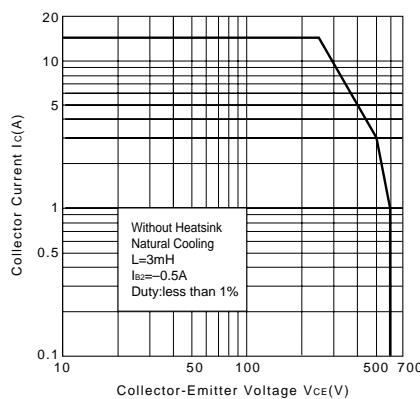
## θ<sub>j-a</sub>-t Characteristics



## Safe Operating Area (Single Pulse)



## Reverse Bias Safe Operating Area



## Pc-Ta Derating

